



MJE13005D-K

Preliminary

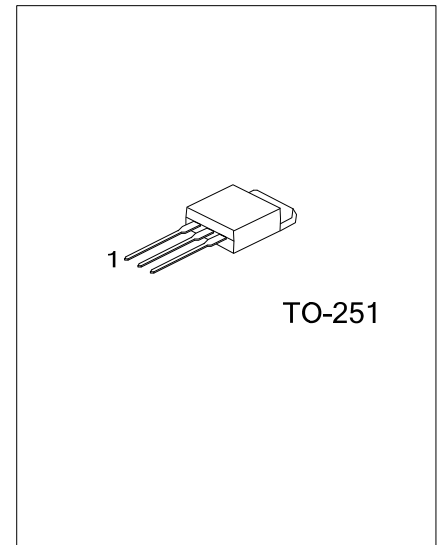
NPN SILICON TRANSISTOR

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

DESCRIPTION

The UTC **MJE13005D-K** is a high voltage fast-switching NPN power transistor. It is characterized by high breakdown voltage, high current capability, high switching speed and high reliability.

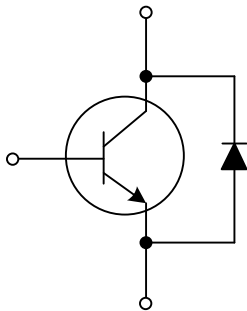
The UTC **MJE13005D-K** is intended to be used in energy-saving light, electronic ballast, high frequency switching power supply, high frequency power transform or common power amplifier, etc.



FEATURES

- * High Breakdown Voltage
- * High Current Capability
- * High Switching Speed
- * High Reliability
- * RoHS-Compliant Product

INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
MJE13005DL-K-x-TM3-T	MJE13005DG-K-x-TM3-T	TO-251	B	C	E	Tube

<p>MJE13005DL-K-x-TM3-T</p>	<p>(1) T: Tube</p> <p>(2) TM3: TO-251</p> <p>(3) x: refer to Classification of h_{FE1}</p> <p>(4) L: Lead Free, G: Halogen Free</p>
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■ ABSOLUTE MAXIMUM RATING ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector- Emitter Voltage ($V_{BE}=0$)	V_{CES}	700	V
Collector-Emitter Voltage ($I_B=0$)	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current	DC	I_C	4
	Pulse	I_{CP}	8
Base Current	DC	I_B	2
	Pulse	I_{BP}	4
Power Dissipation	P_D	44	W
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle < 10%.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	100	$^\circ\text{C/W}$
Junction to Case	θ_{JC}	2.87	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=10\text{mA}, I_B=0$	400			V
Collector -Base Breakdown Voltage	BV_{CBO}	$I_C=1\text{mA}, I_B=0$	700			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=1\text{mA}, I_C=0$	9			V
Collect Cut-off Current	I_{CBO}	$V_{CB}=700\text{V}, I_E=0$			100	μA
Collect Cut-off Current	I_{CEO}	$V_{CE}=400\text{V}, I_B=0$			50	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=9\text{V}, I_C=0$			10	μA
DC Current Gain	h_{FE1}	$V_{CE}=5\text{V}, I_C=500\text{mA}$	15		50	
	h_{FE2}	$V_{CE}=5\text{V}, I_C=2\text{A}$	5			
Collector-Emitter Saturation Voltage	V_{CE}	$I_C=1\text{A}, I_B=0.2\text{A}$			0.5	V
		$I_C=2\text{A}, I_B=0.5\text{A}$			0.6	
		$I_C=4\text{A}, I_B=1\text{A}$			1	
		$I_C=2\text{A}, I_B=0.5\text{A}, T_C=100^\circ\text{C}$			1	
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C=2\text{A}, I_B=0.5\text{A}$			1.6	V
Resistive Load	Fall Time	t_F	$V_{CC}=24\text{V}, I_C=2\text{A}, I_{B1}=-I_{B2}=0.4\text{A}$		0.7	μs
	Storage Time	t_S			4	μs
Current Gain Bandwidth Product	f_T	$V_{CE}=10\text{V}, I_C=0.5\text{A}$	4			MHz
Diode Forward Voltage	V_F	$I_F=1\text{A}$			1.5	V

■ CLASSIFICATION OF h_{FE1}

RANK	A	B	C	D	E
RANGE	15 ~ 20	20 ~ 25	25 ~ 30	30 ~ 40	40 ~ 50

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